

ESD



TVS



TSS



MOV



GDT



PLED

BSS138PW

Product specification

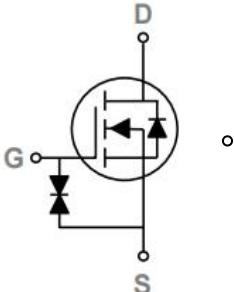
General Features

- 55V,300mA, RDS(ON) = 1.2Ω @VGS = 10V
- Improved dv/dt capability
- Fast switching
- Green Device Available

Application

- Notebook
- Load Switch
- Battery Protection
- Hand-held Instruments

Reference News

PACKAGE OUTLINE	Pin Configuration	Marking
 SOT-323		138W

Absolute Maximum Ratings Tc=25°C unless otherwise noted

Symbol	Parameter	Rating	Units
V _{DS}	Drain-Source Voltage	55	V
V _{GS}	Gate-Source Voltage	±20	V
I _D	Drain Current – Continuous (T _A =25°C)	300	mA
	Drain Current – Continuous (T _A =70°C)	240	mA
I _{DM}	Drain Current – Pulsed ¹	1.2	A
P _D	Power Dissipation (T _A =25°C)	313	mW
	Power Dissipation – Derate above 25°C	2.5	mW/°C
T _{STG}	Storage Temperature Range	-55 to 150	°C
T _J	Operating Junction Temperature Range	-55 to 150	°C

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
R _{θJA}	Thermal Resistance Junction to ambient	---	450	°C/W

Electrical Characteristics (T_J=25 °C , unless otherwise noted)
Off Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =250uA	55	---	---	V
△BV _{DSS} /△T _J	BV _{DSS} Temperature Coefficient	Reference to 25°C , I _D =1mA	---	0.05	---	V/°C
I _{DSS}	Drain-Source Leakage Current	V _{DS} =48V , V _{GS} =0V , T _J =25°C	---	---	1	uA
		V _{DS} =55V , V _{GS} =0V , T _J =85°C	---	---	400	A
I _{GSS}	Gate-Source Leakage Current	V _{GS} = ±20V , V _{DS} =0V	---	---	±6	uA

On Characteristics

R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =10V , I _D =0.3A	---	1.2	1.5	Ω
		V _{GS} =4.5V , I _D =0.2A	---	1.5	2.3	
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250uA	0.8	1.1	1.6	V
△V _{GS(th)}	V _{GS(th)} Temperature Coefficient		---	3	---	mV/°C

On Characteristics

R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =10V , I _D =0.3A	---	1.2	1.5	Ω
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△V _{GS(th)}	V _{GS(th)} Temperature Coefficient		---	3	---	mV/°C

Dynamic and switching Characteristics

C _{iss}	Input Capacitance	V _{DS} =30V , V _{GS} =0V , F=1MHz	---	23	---	pF
C _{oss}	Output Capacitance		---	16	---	
C _{rss}	Reverse Transfer Capacitance		---	10	---	

Drain-Source Diode Characteristics and Maximum Ratings

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _S	Continuous Source Current	V _G =V _D =0V , Force Current	---	---	300	mA
I _{SM}	Pulsed Source Current		---	---	600	mA
V _{SD}	Diode Forward Voltage	V _{GS} =0V , I _S =0.3A , T _J =25°C	---	---	1.4	V

Note :

- 1 . Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. The data tested by pulsed , pulse width \leq 300us , duty cycle \leq 2% .
3. Essentially independent of operating temperature.

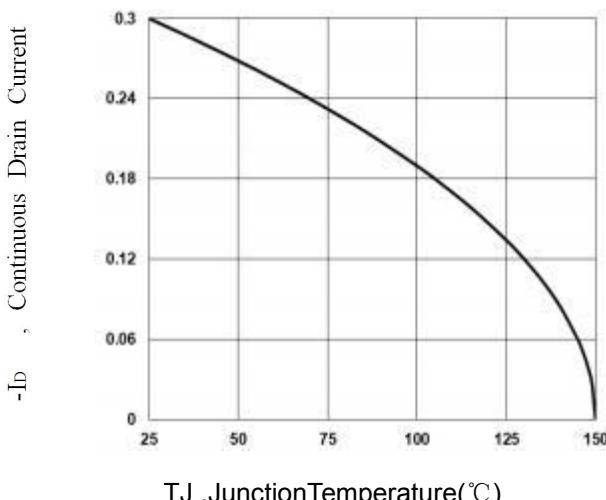


Fig. 1 Continuous Drain Current vs. T_J

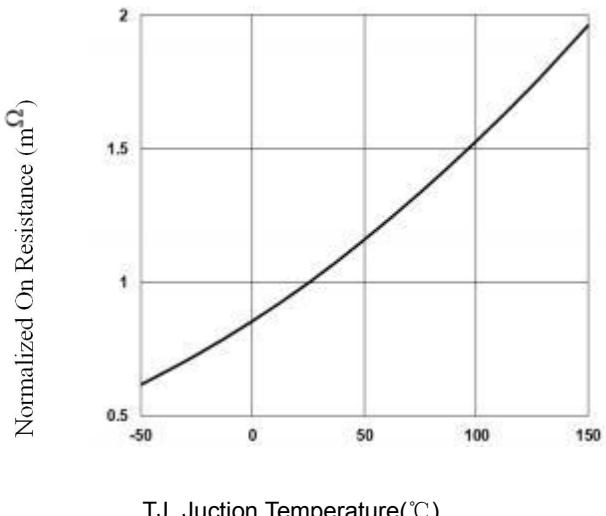


Fig. 2 Normalized $R_{DS(on)}$ vs. T_J

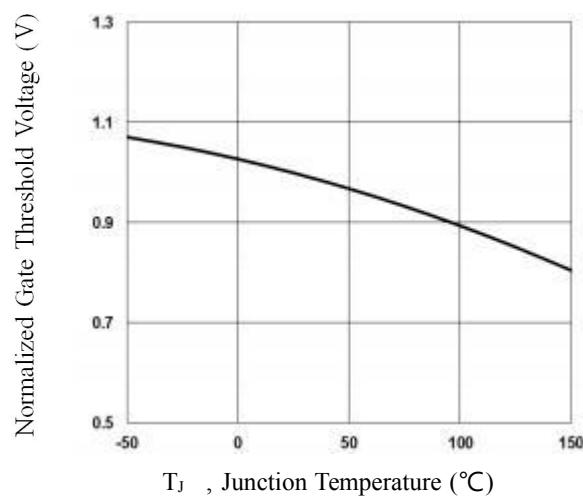


Fig. 3 Normalized V_{th} vs. T_J

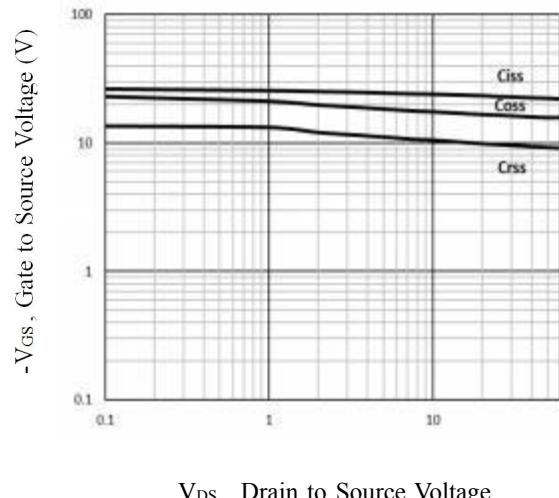


Fig. 4 Capacitance Characteristics

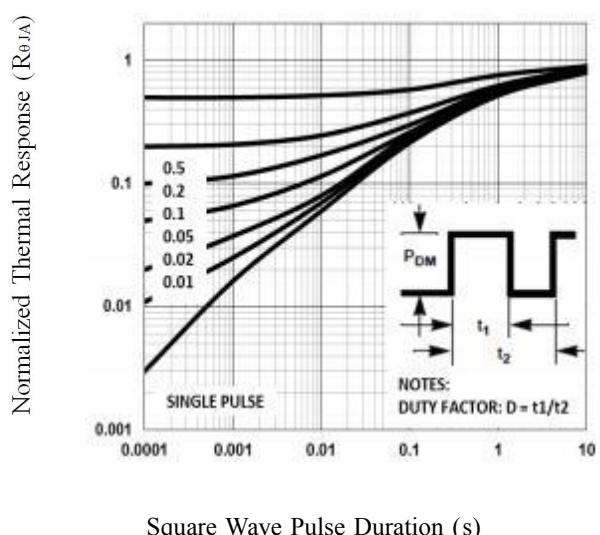


Fig. 5 Normalized Transient Response

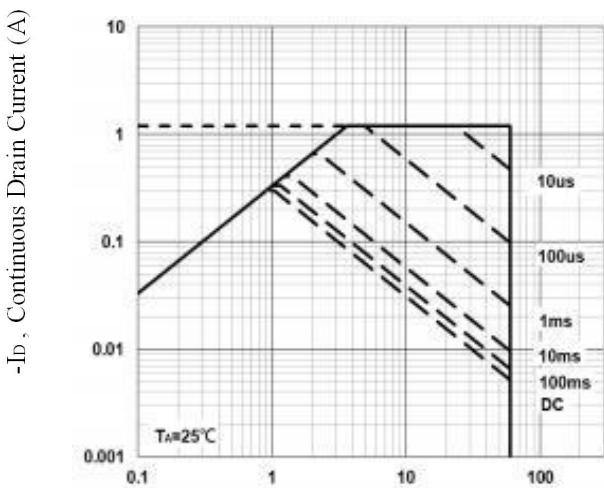
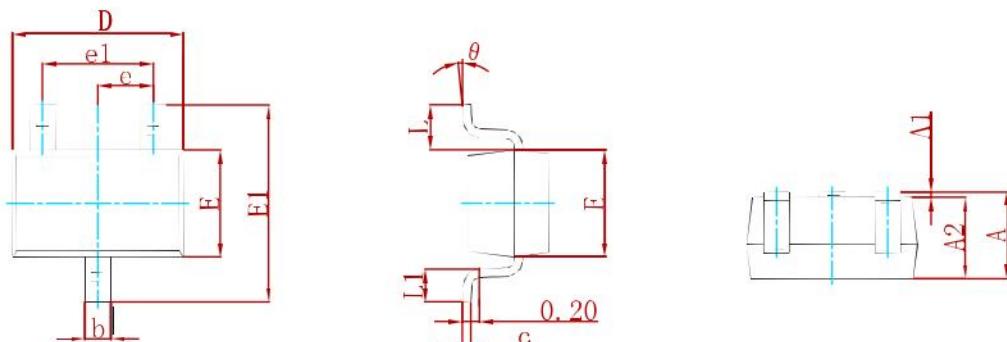
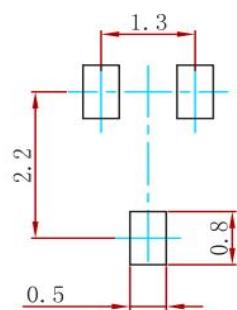


Fig. 6 Maximum Safe Operation Area

PACKAGE MECHANICAL DATA


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.100	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.000	0.035	0.039
b	0.200	0.400	0.008	0.016
c	0.080	0.150	0.003	0.006
D	2.000	2.200	0.079	0.087
E	1.150	1.350	0.045	0.053
E1	2.150	2.450	0.085	0.096
e	0.650 TYP		0.026 TYP	
e1	1.200	1.400	0.047	0.055
L	0.525 REF		0.021 REF	
L1	0.260	0.460	0.010	0.018
9	0°	8°	0°	8°

Suggested Pad Layout


Note:
 1. Controlling dimension:in millimeters.
 2.General tolerance: ± 0.05 mm.
 3.The pad layout is for reference purposes only.

REEL SPECIFICATION

P/N	PKG	QTY
BSS138PW	SOT-323	3000

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